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3. (original) The method of claim 1, wherein the step of providing a semiconductor wafer includes a semiconductor wafer having residual sulfur containing contaminants.

4. (cancelled)

B 5. (original) The method of claim A, wherein the alkaline solution includes deionized water and at least one ammonia free base.

6. (original) The method of claim 5, wherein the at least one ammonia free base includes sodium hydroxide.

7. (original) The method of claim 1, wherein the step of exposing the process surfaces to an alkaline solution includes at least one of a dipping and spraying process.

8. (original) The method of claim 7, wherein the dipping process is carried out with simultaneous application of megasonic energy and the spraying process carried out with simultaneous spinning of the semiconductor wafer.